

Search Hist. (7 pp) ~~7/17/05~~ (10/17/05)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	9458	((257/213) or (257/239) or (257/288) or (257/261) or (257/314) or (257/315) or (257/E21.179) or (257/E21.422) or (365/185.12) or (365/185.13) or (365/185.17) or (365/185.18) or (365/185.29)).CCLS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 16:43
L2	29	1 and floating and (halo counter adj dop\$3 buried) near10 (punch adj "through")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 16:44
S1	5	"753673".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 12:08
S2	2	("5761121").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 07:16
S3	2	EP-776049\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 07:19
S4	2	("5912842").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 07:23
S5	0	("two-transistor near3 (PMOS PMOS FET)").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 07:24
S6	2	two-transistor near3 (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 07:29
S7	574	common adj (drain source "source/drain") and floating adj gate and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 07:30

S8	115	common adj (drain source "source/drain") and floating adj gate and (PMOS PMOSFET) and select adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 07:31
S9	115	common adj (drain source "source/drain") and floating adj gate and (PMOS PMOSFET) and select adj gate and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 07:54
S10	10	implant near6 common near2 (drain source "source/drain") and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 07:55
S11	10	(halo implant) near6 common near2 (drain source "source/drain") and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 07:55
S12	2	(US-6207991-\$ or US-5877051-\$). did.	USPAT	OR	OFF	2005/02/22 08:04
S13	12	(US-20050030827-\$ or US-20030034510-\$).did. or (US-5761121-\$ or US-5912842-\$ or US-5943265-\$ or US-5687118-\$ or US-6207991-\$ or US-5877051-\$ or US-6146936-\$).did. or (EP-776049-\$ or WO-9919880-\$). did. or (EP-776049-\$).did.	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2005/02/22 08:08
S14	215	two adj transistor near4 memory adj cell	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2005/02/22 08:08
S15	99	two adj transistor near4 memory adj cell and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2005/02/22 08:09
S16	99	two adj transistor near4 memory adj cell and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:13
S17	249	implant and (punch-through punch adj "through") and common adj (source drain "source/drain")	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:15
S18	190	implant and (punch-through punch adj "through") and common adj (source drain "source/drain") and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:15

S19	39	implant and (punch-through punch adj "through") and common adj (source drain "source/drain") and memory and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:22
S20	39	(halo implant) and (punch-through punch adj "through") and common adj (source drain "source/drain") and memory and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:24
S21	0	halo near6 punch-through and halo near6 common near2 (source-drain source/drain drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:25
S22	6	halo near6 (punchthrough punch adj through punch-through) and common near2 (source-drain source/drain drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:42
S23	7	chang.in. and S13	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 08:52
S24	2	S23 and polysilicon and (bit adj line bitline bit adj line) and floating adj gate and select adj gate and (tunneling tunnelling) near3 (Fowler Nordheim) and (thick thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 09:39
S25	1	S23 and polysilicon and (bit adj line bitline bit adj line) and control adj gate near6 polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 09:52
S26	0	S23 and polysilicon and floating adj gate and control adj gate near6 (body adj bias back-gate back adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 09:53
S27	49	control adj gate near6 (body adj bias back-gate back adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 09:54
S28	26	control adj gate near6 (body adj bias back-gate back adj gate) and floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 09:55
S29	7	control adj gate near6 (body adj bias back-gate back adj gate) and floating adj gate and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/22 09:56

S30	12	(US-20050030827-\$ or US-20030034510-\$).did. or (US-5761121-\$ or US-5912842-\$ or US-5943265-\$ or US-5687118-\$ or US-6207991-\$ or US-5877051-\$ or US-6146936-\$).did. or (EP-776049-\$ or WO-9919880-\$). did. or (EP-776049-\$).did.	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2005/02/22 10:27
S31	0	S30 and (thick thickness) near4 (drain source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 10:28
S32	1	S30 and (depth thick thickness) near4 (drain source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 10:30
S33	33	(depth thick thickness) near4 (drain source) and floating adj gate and halo	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 10:50
S34	278	"100" near2 kev near10 phosphorus same implantation and (depth thickness thick)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 10:52
S35	12	"100" near2 kev near10 phosphorus near10 (depth thickness) same implantation and (depth thickness thick)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 11:09
S36	5789	((257/213) or (257/239) or (257/288) or (257/261) or (257/314) or (257/315) or (257/e21.179) or (257/e21.422) or (257/e21.68)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 11:10
S37	15	S36 and (halo implant) and floating adj gate and punch adj through and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 11:12
S38	1151	(365/185\$2).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 11:12

S39	5	S38 and (halo implant) and floating adj gate and punch adj through and (PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/22 11:12
S40	718	halo adj implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 12:09
S41	48	halo adj implant and floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 12:20
S42	310	(counter-doped halo) and floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 12:21
S43	383	(counter adj dop\$3 halo) and floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 12:21
S44	398	(counter adj dop\$3 halo) and floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 12:47
S45	0	floating adj gate near20 (logic\$2 address select) adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 12:47
S46	1149	floating adj gate near20 ((logic\$2 address select) adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 12:48
S47	0	floating adj gate near20 ((logic\$2 address select) adj gate) and halo near4 "only"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 12:48
S48	0	floating adj gate near20 ((logic\$2 address select) adj gate) and halo near4 ("exclusively" "only")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 12:48

S49	0	floating adj gate near20 ((logic\$2 address select) adj gate) and halo near4 ("exclusively" "only" "one" adj side)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 12:49
S50	27	floating adj gate near20 ((logic\$2 address select) adj gate) and halo	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 13:09
S51	184	floating adj gate near20 ((logic\$2 address select) adj gate) and buried	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 13:40
S52	0	floating adj gate near20 ((logic\$2 address select) adj gate) and counter adj doping	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 13:40
S53	203	floating adj gate near20 ((logic\$2 address select) adj gate) and (counter adj dop\$3 buried halo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 14:04
S54	7	punch adj "through" near6 (oxynitride ONO roxnox)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 14:08
S55	2	("6180443").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 14:08
S56	2	S55 and implant\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 14:10
S57	304	floating near1 gate and (select logic\$2 address) near1 gate and punch adj through	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 14:13
S58	1062	floating near1 gate and (control select logic\$2 address) near1 gate and punch adj through	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 14:14

S59	1802	floating near1 gate and (control select logic\$2 address) near1 gate and (over adj erase punch adj through)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 14:14
S60	1802	floating near1 gate and (control select logic\$2 address) near1 gate and ("over" adj erase punch adj through)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 14:14
S61	500	floating near1 gate and (control select logic\$2 address) near1 gate and ("over" adj erase punch adj through) and (buried counter adj dop\$3 halo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 14:17
S62	2	("5912842").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 16:42